

L Number	Hits	Search Text	DB	Time stamp
1	43	438/257.CCLS. AND (memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 or quarter adj micron adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/13 16:25
2	43	257/315,316.CCLS. AND 438/257.CCLS. AND (memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 or quarter adj micron adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/13 16:26
-	790596	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/10 17:09
-	1819	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/10 14:38
-	53	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/11 19:01
-	791060	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/10 17:10
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 adj micron adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/11 19:02
-	43	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 or quarter adj micron adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/13 16:24
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.25 or quarter) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/11 19:04
-	15	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.25 or quarter) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:35
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.25 or quarter) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/11 19:28
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.18 or quarter) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:32
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.18) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:33
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.18) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:33
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.15) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:33

-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.1) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:33
-	0	(.1) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:34
-	0	(.18) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:34
-	0	(.25) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:34
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.25) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:35
-	15	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.25 or quarter) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:36
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.25) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:36